

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CBR6M-L010M SERIES

GLASS PASSIVATED JUNCTION
SILICON BRIDGE RECTIFIER
6.0 AMP, 100 THRU 1000 VOLTS

CASE DMM

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR6M-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose, high current applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

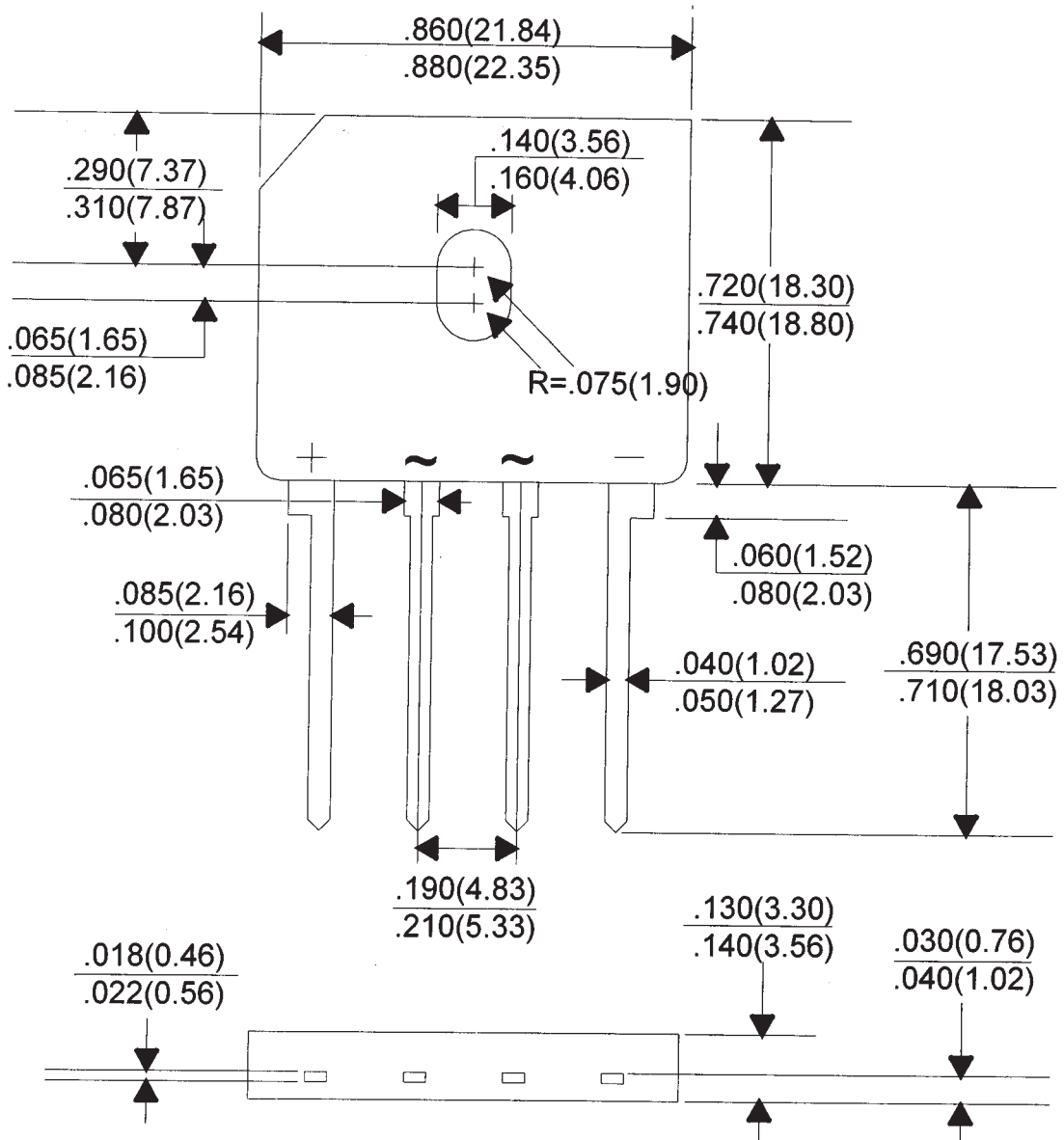
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>	CBR6M <u>-L010M</u>	CBR6M <u>-L020M</u>	CBR6M <u>-L040M</u>	CBR6M <u>-L060M</u>	CBR6M <u>-L080M</u>	CBR6M <u>-L100M</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_C=100^\circ\text{C}$)	I_O				6.0			A
Peak Forward Surge Current	I_{FSM}				175			A
Operating and Storage Junction Temperature	T_J, T_{stg}				-65 to +150			$^\circ\text{C}$
Thermal Resistance	θ_{JC}				3.1			$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I_R	V_R =Rated V_{RRM}			5.0	μA
I_R	V_R =Rated V_{RRM} , $T_C=100^\circ\text{C}$			500	μA
V_F	$I_F=6.0\text{A}$			1.0	V
C_J	$V_R=4.0\text{V}$, $f=1.0\text{MHz}$		260		pF

CASE DMM - MECHANICAL OUTLINE



All Dimensions in Inches (mm).